



Sheet 1 of 1

Form 1449*

Atty. Docket No.: 303.691US1

Serial No. 09/584,566

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT


Applicant: Leonard Forbes et al.

(Use several sheets if necessary)

Filing Date: May 31, 2000

Group: 2818

U.S. PATENT DOCUMENTS

**Examiner		Document Number	Date	Name	Class	Subclass	Filing Date
Initial							If Appropriate
		5,386,132	01/01/1995	Wong	257	316	
		5,583,360	10/01/1996	Ruth, et al.	257	316	
		5,847,425	12/01/1998	Yuan, et al.	257	315	

FOREIGN PATENT DOCUMENTS

**Examiner		Document Number	Date	Country	Class	Subclass	Translation	
Initial							Yes	No

OTHER DOCUMENTS

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Sheet 1 of 2

Form 1449*	Atty. Docket No.: 303.691US1	Serial No. 09/584,566
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U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	4,051,354	09/27/1977	Choate, W.C.	235	312	07/03/75
	5,327,380	07/05/1994	Kersh, III, D.V., et al.	365	195	02/08/91
	5,661,055	08/26/1997	Hsu, J.J., et al.	438	259	06/07/95
	5,991,225	11/23/1999	Forbes, L., et al.	365	230.06	02/27/98

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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OTHER DOCUMENTS

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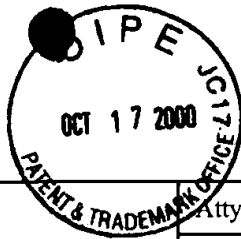
	"Frequently-Asked Questions (FAQ) About Programmable Logic", <u>OptiMagic, Inc.</u> , http://www.optimagic.com/faq.html , pp. 1-18, (1997)
	Chen, W., et al., "Very uniform and high aspect ratio anisotropy SiO2 etching process in magnetic neutral loop discharge plasma", <u>J. Vac. Sci. Technol. A</u> , 17(5), pp. 2546-2550, (1999)
	Dipert, B., et al., "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30, 48-52, (October 1993)
	Hodges, D.A., et al., <u>Analysis and Design of Digital Integrated Circuits</u> , McGraw-Hill Book Company, 2nd Edition, 394-396, (1988)
	Hodges, D.A., et al., <u>Analysis and Design of Digital Integrated Circuits</u> , 2nd Edition, McGraw-Hill Publishing, New York, pp. 354-357, (1988)
	Johnson, J., et al., "IBM's 0.5 micrometer Embedded Flash Memory Technology", <u>MicroNews</u> , 4(3), http://www.chips.ibm.com/micronews/vol14_no3/flash.html , pp. 1-7, (1998)
	Landheer, D., et al., "Formation of high-quality silicon dioxide films by electron cyclotron resonance plasma oxidation and plasma-enhanced chemical vapour deposition", <u>Thin Solid Films</u> , 293, pp. 52-62, (1997)
	Moore, W.R., "A Review of Fault-Tolerant Techniques for the Enhancement of Integrated Circuit Yield", <u>Proceedings of the IEEE</u> , 74(5), 684-698, (May 1986)

Examiner

Date Considered

*Substitute Disclosure Statement Form (PTO-1449)

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Initial

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Nozawa, R., et al., "Low temperature polycrystalline silicon film formation with and without charged species in an electron cyclotron resonance SiH₄/H₂ plasma-enhanced chemical vapor deposition", J. Vac. Sci. Technol. A, 17(5), pp. 2542-2545, (1999)

Patel, P., et al., "Low temperature VUV enhanced growth of thin silicon dioxide films", Applied Surface Science, 46, pp.352-356, (1990)

Rueger, N.R., et al., "Selective etching of SiO₂ over polycrystalline silicon using CHF₃ in an inductively coupled plasma", J. Vac. Sci. Technol. A, 17(5), pp. 2492-2502, (1999)

Shindo, W., et al., "Low-temperature large-grain poly-Si direct deposition by microwave plasma enhanced chemical vapor disposition using SiH₄/Xe", J. Vac. Sci. Technol. A, 17(5), pp. 3134-3138, (1999)

Usami, K., et al., "Thin Si Oxide films for MIS tunnel emitter by hollow cathode enhanced plasma", Thin Films, 281-282, pp. 412-414, (1996)

Vallon, S., et al., "Polysilicon-germanium gate patterning studies in a high density plasma helicon source", J. Vac. Sci. Technol. A, 15(4), pp. 1874-1880, (1997)

Examiner

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